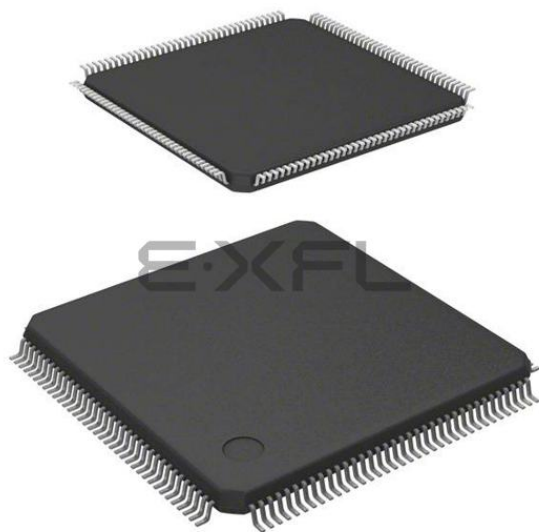




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Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	112
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 21x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103zet6

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Figure 8. STM32F103xC/D/E performance line
WLCSP64 ballout, ball side

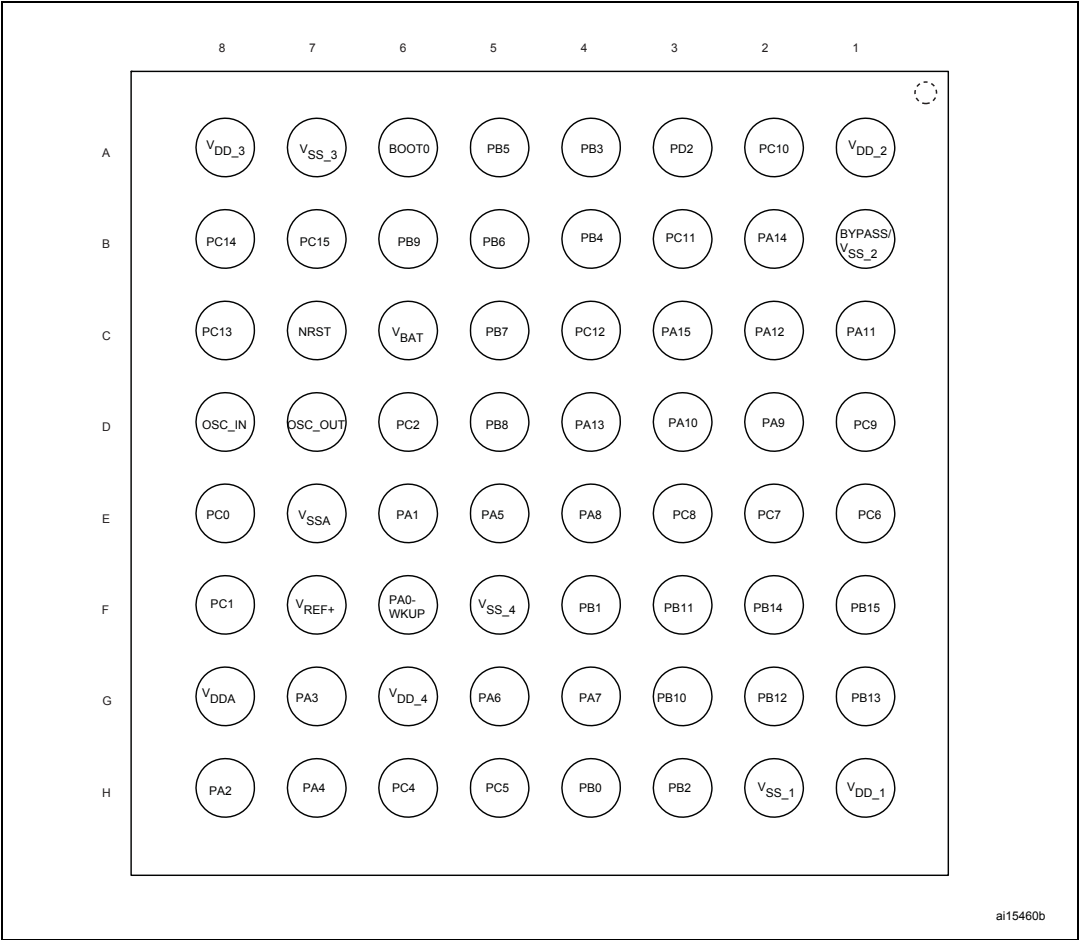


Table 5. High-density STM32F103xC/D/E pin definitions (continued)

Pins						Pin name	Type ⁽¹⁾	I / O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Alternate functions ⁽⁴⁾	
LFBGA144	LFBGA100	WLCSP64	LQFP64	LQFP100	LQFP144					Default	Remap
L4	J4	H4	26	35	46	PB0	I/O	-	PB0	ADC12_IN8/TIM3_CH3 TIM8_CH2N	TIM1_CH2N
M4	K4	F4	27	36	47	PB1	I/O	-	PB1	ADC12_IN9/TIM3_CH4 ⁽⁹⁾ TIM8_CH3N	TIM1_CH3N
J5	G5	H3	28	37	48	PB2	I/O	FT	PB2/BOOT1	-	-
M5	-	-	-	-	49	PF11	I/O	FT	PF11	FSMC_NIOS16	-
L5	-	-	-	-	50	PF12	I/O	FT	PF12	FSMC_A6	-
H5	-	-	-	-	51	V _{SS_6}	S	-	V _{SS_6}	-	-
G5	-	-	-	-	52	V _{DD_6}	S	-	V _{DD_6}	-	-
K5	-	-	-	-	53	PF13	I/O	FT	PF13	FSMC_A7	-
M6	-	-	-	-	54	PF14	I/O	FT	PF14	FSMC_A8	-
L6	-	-	-	-	55	PF15	I/O	FT	PF15	FSMC_A9	-
K6	-	-	-	-	56	PG0	I/O	FT	PG0	FSMC_A10	-
J6	-	-	-	-	57	PG1	I/O	FT	PG1	FSMC_A11	-
M7	H5	-	-	38	58	PE7	I/O	FT	PE7	FSMC_D4	TIM1_ETR
L7	J5	-	-	39	59	PE8	I/O	FT	PE8	FSMC_D5	TIM1_CH1N
K7	K5	-	-	40	60	PE9	I/O	FT	PE9	FSMC_D6	TIM1_CH1
H6	-	-	-	-	61	V _{SS_7}	S	-	V _{SS_7}	-	-
G6	-	-	-	-	62	V _{DD_7}	S	-	V _{DD_7}	-	-
J7	G6	-	-	41	63	PE10	I/O	FT	PE10	FSMC_D7	TIM1_CH2N
H8	H6	-	-	42	64	PE11	I/O	FT	PE11	FSMC_D8	TIM1_CH2
J8	J6	-	-	43	65	PE12	I/O	FT	PE12	FSMC_D9	TIM1_CH3N
K8	K6	-	-	44	66	PE13	I/O	FT	PE13	FSMC_D10	TIM1_CH3
L8	G7	-	-	45	67	PE14	I/O	FT	PE14	FSMC_D11	TIM1_CH4
M8	H7	-	-	46	68	PE15	I/O	FT	PE15	FSMC_D12	TIM1_BKIN
M9	J7	G3	29	47	69	PB10	I/O	FT	PB10	I2C2_SCL/USART3_TX ⁽⁹⁾	TIM2_CH3
M10	K7	F3	30	48	70	PB11	I/O	FT	PB11	I2C2_SDA/USART3_RX ⁽⁹⁾	TIM2_CH4
H7	E7	H2	31	49	71	V _{SS_1}	S	-	V _{SS_1}	-	-
G7	F7	H1	32	50	72	V _{DD_1}	S	-	V _{DD_1}	-	-

Table 5. High-density STM32F103xC/D/E pin definitions (continued)

Pins						Pin name	Type ⁽¹⁾	I / O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Alternate functions ⁽⁴⁾	
LFBGA144	LFBGA100	WLCSP64	LQFP64	LQFP100	LQFP144					Default	Remap
A5	D4	-	-	97	141	PE0	I/O	FT	PE0	TIM4_ETR / FSMC_NBL0	-
A4	C4	-	-	98	142	PE1	I/O	FT	PE1	FSMC_NBL1	-
E5	E5	A7	63	99	143	V _{SS_3}	S	-	V _{SS_3}	-	-
F5	F5	A8	64	100	144	V _{DD_3}	S	-	V _{DD_3}	-	-

1. I = input, O = output, S = supply.

2. FT = 5 V tolerant.

3. Function availability depends on the chosen device.

4. If several peripherals share the same I/O pin, to avoid conflict between these alternate functions only one peripheral should be enabled at a time through the peripheral clock enable bit (in the corresponding RCC peripheral clock enable register).

5. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited: the speed should not exceed 2 MHz with a maximum load of 30 pF and these IOs must not be used as a current source (e.g. to drive an LED).

6. Main function after the first backup domain power-up. Later on, it depends on the contents of the Backup registers even after reset (because these registers are not reset by the main reset). For details on how to manage these IOs, refer to the Battery backup domain and BKP register description sections in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.

7. In the WCLSP64 package, the PC3 I/O pin is not bonded and it must be configured by software to output mode (Push-pull) and writing 0 to the data register in order to avoid an extra consumption during low-power modes.

8. Unlike in the LQFP64 package, there is no PC3 in the WLCSP package. The V_{REF+} functionality is provided instead.

9. This alternate function can be remapped by software to some other port pins (if available on the used package). For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.

10. For the WCLSP64/LQFP64 package, the pins number 5 and 6 are configured as OSC_IN/OSC_OUT after reset, however the functionality of PD0 and PD1 can be remapped by software on these pins. For the LQFP100/BGA100 and LQFP144/BGA144 packages, PD0 and PD1 are available by default, so there is no need for remapping. For more details, refer to Alternate function I/O and debug configuration section in the STM32F10xxx reference manual.

11. For devices delivered in LQFP64 packages, the FSMC function is not available.

Table 6. FSMC pin definition

Pins	FSMC					LQFP100 BGA100 ⁽¹⁾
	CF	CF/IDE	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND 16 bit	
PE2	-	-	A23	A23	-	Yes
PE3	-	-	A19	A19	-	Yes
PE4	-	-	A20	A20	-	Yes
PE5	-	-	A21	A21	-	Yes
PE6	-	-	A22	A22	-	Yes
PF0	A0	A0	A0	-	-	-
PF1	A1	A1	A1	-	-	-
PF2	A2	A2	A2	-	-	-
PF3	A3	-	A3	-	-	-
PF4	A4	-	A4	-	-	-
PF5	A5	-	A5	-	-	-
PF6	NIORD	NIORD	-	-	-	-
PF7	NREG	NREG	-	-	-	-
PF8	NIOWR	NIOWR	-	-	-	-
PF9	CD	CD	-	-	-	-
PF10	INTR	INTR	-	-	-	-
PF11	NIOS16	NIOS16	-	-	-	-
PF12	A6	-	A6	-	-	-
PF13	A7	-	A7	-	-	-
PF14	A8	-	A8	-	-	-
PF15	A9	-	A9	-	-	-
PG0	A10	-	A10	-	-	-
PG1	-	-	A11	-	-	-
PE7	D4	D4	D4	DA4	D4	Yes
PE8	D5	D5	D5	DA5	D5	Yes
PE9	D6	D6	D6	DA6	D6	Yes
PE10	D7	D7	D7	DA7	D7	Yes
PE11	D8	D8	D8	DA8	D8	Yes
PE12	D9	D9	D9	DA9	D9	Yes
PE13	D10	D10	D10	DA10	D10	Yes
PE14	D11	D11	D11	DA11	D11	Yes
PE15	D12	D12	D12	DA12	D12	Yes
PD8	D13	D13	D13	DA13	D13	Yes

Table 14. Maximum current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions	f _{HCLK}	Max ⁽¹⁾		Unit
				T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled	72 MHz	69	70	mA
			48 MHz	50	50.5	
			36 MHz	39	39.5	
			24 MHz	27	28	
			16 MHz	20	20.5	
			8 MHz	11	11.5	
		External clock ⁽²⁾ , all peripherals disabled	72 MHz	37	37.5	
			48 MHz	28	28.5	
			36 MHz	22	22.5	
			24 MHz	16.5	17	
			16 MHz	12.5	13	
			8 MHz	8	8	

1. Guaranteed by characterization results.

2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Table 15. Maximum current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions	f _{HCLK}	Max ⁽¹⁾		Unit
				T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled	72 MHz	66	67	mA
			48 MHz	43.5	45.5	
			36 MHz	33	35	
			24 MHz	23	24.5	
			16 MHz	16	18	
			8 MHz	9	10.5	
		External clock ⁽²⁾ , all peripherals disabled	72 MHz	33	33.5	
			48 MHz	23	23.5	
			36 MHz	18	18.5	
			24 MHz	13	13.5	
			16 MHz	10	10.5	
			8 MHz	6	6.5	

1. Guaranteed by characterization results at V_{DD} max, f_{HCLK} max.

2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

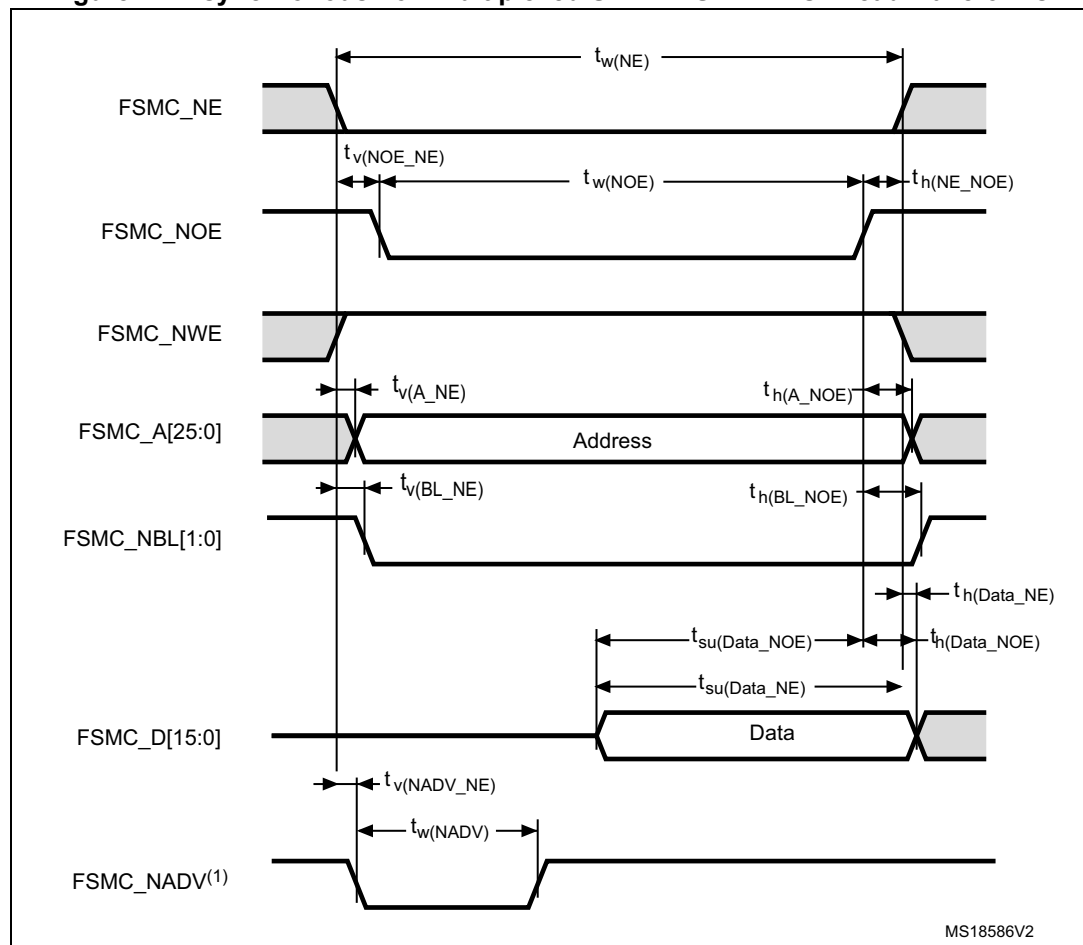
5.3.10 FSMC characteristics

Asynchronous waveforms and timings

Figure 24 through Figure 27 represent asynchronous waveforms and Table 31 through Table 34 provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- AddressSetupTime = 0
- AddressHoldTime = 1
- DataSetupTime = 1

Figure 24. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms



1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

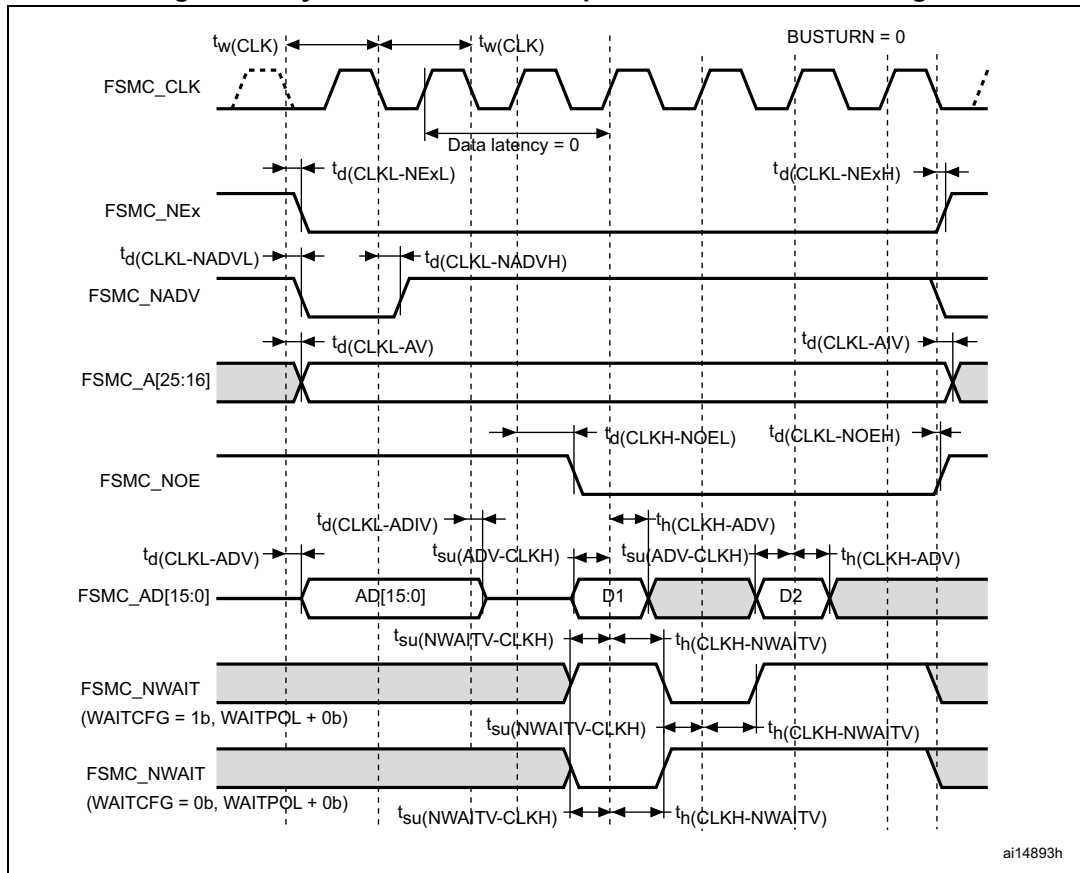
Table 34. Asynchronous multiplexed PSRAM/NOR write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{h(AD_NADV)}$	FSMC_AD (address) valid hold time after FSMC_NADV high	$t_{HCLK} - 3$	-	ns
$t_{h(A_NWE)}$	Address hold time after FSMC_NWE high	$4t_{HCLK}$	-	ns
$t_{v(BL_NE)}$	FSMC_NEx low to FSMC_BL valid	-	1.6	ns
$t_{h(BL_NWE)}$	FSMC_BL hold time after FSMC_NWE high	$t_{HCLK} - 1.5$	-	ns
$t_{v(Data_NADV)}$	FSMC_NADV high to Data valid	-	$t_{HCLK} + 1.5$	ns
$t_{h(Data_NWE)}$	Data hold time after FSMC_NWE high	$t_{HCLK} - 5$	-	ns

1. $C_L = 15$ pF.

2. BGuaranteed by characterization results.

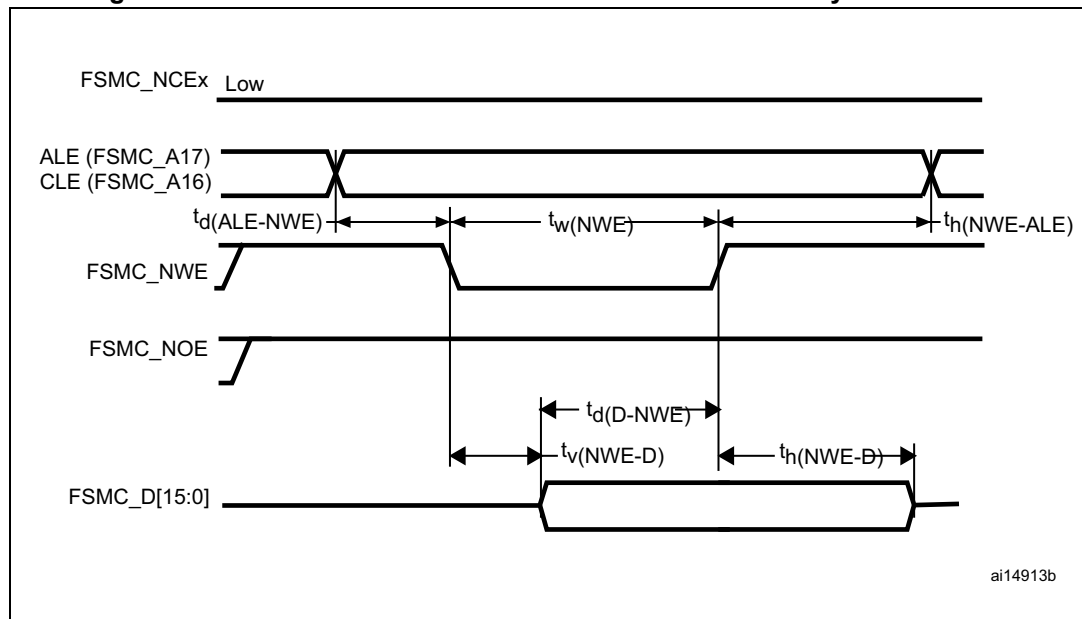
Figure 31. Synchronous non-multiplexed PSRAM write timings

Table 38. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_w(\text{CLK})$	FSMC_CLK period	27.7	-	ns
$t_d(\text{CLKL-NExL})$	FSMC_CLK low to FSMC_NEx low ($x = 0 \dots 2$)	-	2	ns
$t_d(\text{CLKL-NExH})$	FSMC_CLK low to FSMC_NEx high ($x = 0 \dots 2$)	2	-	ns
$t_d(\text{CLKL-NADVL})$	FSMC_CLK low to FSMC_NADV low	-	4	ns
$t_d(\text{CLKL-NADVH})$	FSMC_CLK low to FSMC_NADV high	5	-	ns
$t_d(\text{CLKL-AV})$	FSMC_CLK low to FSMC_Ax valid ($x = 16 \dots 25$)	-	0	ns
$t_d(\text{CLKL-AIV})$	FSMC_CLK low to FSMC_Ax invalid ($x = 16 \dots 25$)	2	-	ns
$t_d(\text{CLKL-NWEL})$	FSMC_CLK low to FSMC_NWE low	-	1	ns
$t_d(\text{CLKL-NWEH})$	FSMC_CLK low to FSMC_NWE high	1	-	ns
$t_d(\text{CLKL-Data})$	FSMC_D[15:0] valid data after FSMC_CLK low	-	6	ns
$t_d(\text{CLKL-NBLH})$	FSMC_CLK low to FSMC_NBL high	1	-	ns
$t_{su}(\text{NWAITV-CLKH})$	FSMC_NWAIT valid before FSMC_CLK high	7	-	ns
$t_h(\text{CLKH-NWAITV})$	FSMC_NWAIT valid after FSMC_CLK high	2	-	ns

1. $C_L = 15 \text{ pF}$.

2. Guaranteed by characterization results.

Figure 41. NAND controller waveforms for common memory write access**Table 40. Switching characteristics for NAND Flash read and write cycles⁽¹⁾**

Symbol	Parameter	Min	Max	Unit
$t_{d(D-NWE)}^{(2)}$	FSMC_D[15:0] valid before FSMC_NWE high	$5t_{HCLK} + 12$	-	ns
$t_{w(NOE)}^{(2)}$	FSMC_NWE low width	$4t_{HCLK}-1.5$	$4t_{HCLK}+1.5$	ns
$t_{su(D-NOE)}^{(2)}$	FSMC_D[15:0] valid data before FSMC_NOE high	25	-	ns
$t_{h(NOE-D)}^{(2)}$	FSMC_D[15:0] valid data after FSMC_NOE high	7	-	-
$t_{w(NWE)}^{(2)}$	FSMC_NWE low width	$4t_{HCLK}-1$	$4t_{HCLK}+1$	ns
$t_{v(NWE-D)}^{(2)}$	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
$t_{h(NWE-D)}^{(2)}$	FSMC_NWE high to FSMC_D[15:0] invalid	$2t_{HCLK} + 4$	-	ns
$t_{d(ALE-NWE)}^{(3)}$	FSMC_ALE valid before FSMC_NWE low	-	$3t_{HCLK} + 1.5$	ns
$t_{h(NWE-ALE)}^{(3)}$	FSMC_NWE high to FSMC_ALE invalid	$3t_{HCLK} + 4.5$	-	ns
$t_{d(ALE-NOE)}^{(3)}$	FSMC_ALE valid before FSMC_NOE low	-	$3t_{HCLK} + 2$	ns
$t_{h(NOE-ALE)}^{(3)}$	FSMC_NWE high to FSMC_ALE invalid	$3t_{HCLK} + 4.5$	-	ns

1. $C_L = 15$ pF.

2. Guaranteed by characterization results.

3. Guaranteed by design.

5.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB: A Burst of Fast Transient voltage** (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 41](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 41. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP144, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 72\text{ MHz}$ conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP144, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 72\text{ MHz}$ conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

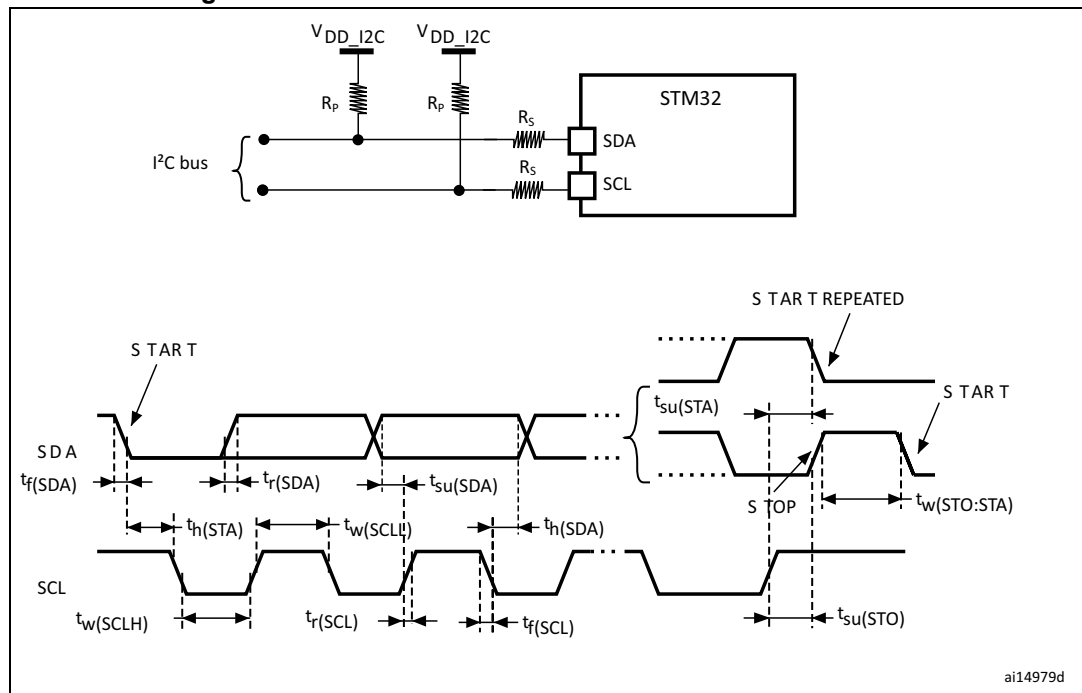
Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

Figure 48. I²C bus AC waveforms and measurement circuit

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.
2. R_s : Series protection resistors.
3. R_p : Pull-up resistors.
4. V_{DD_I2C} : I²C bus supply

Table 52. SCL frequency ($f_{PCLK1} = 36 \text{ MHz}$, $V_{DD_I2C} = 3.3 \text{ V}$)⁽¹⁾⁽²⁾

f_{SCL} (kHz)	I2C_CCR value
	$R_p = 4.7 \text{ k}\Omega$
400	0x801E
300	0x8028
200	0x803C
100	0x00B4
50	0x0168
20	0x0384

1. R_p = External pull-up resistance, f_{SCL} = I²C speed.
2. For speeds around 200 kHz, the tolerance on the achieved speed is of $\pm 5\%$. For other speed ranges, the tolerance on the achieved speed $\pm 2\%$. These variations depend on the accuracy of the external components used to design the application.

I²S - SPI characteristics

Unless otherwise specified, the parameters given in [Table 53](#) for SPI or in [Table 54](#) for I²S are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 10](#).

Refer to [Section 5.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Table 53. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_c(SCK)$	SPI clock frequency	Master mode	-	18	MHz
		Slave mode	-	18	
$t_r(SCK)$ $t_f(SCK)$	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}^{(1)}$	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}^{(1)}$	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCKH)}^{(1)}$ $t_{w(SCKL)}^{(1)}$	SCK high and low time	Master mode, $f_{PCLK} = 36$ MHz, presc = 4	50	60	
$t_{su(MI)}^{(1)}$ $t_{su(SI)}^{(1)}$	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}^{(1)}$ $t_{h(SI)}^{(1)}$	Data input hold time	Master mode	5	-	
		Slave mode	4	-	
$t_{a(SO)}^{(1)(2)}$	Data output access time	Slave mode, $f_{PCLK} = 20$ MHz	0	$3t_{PCLK}$	
$t_{dis(SO)}^{(1)(3)}$	Data output disable time	Slave mode	2	10	
$t_{v(SO)}^{(1)}$	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}^{(1)}$	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}^{(1)}$ $t_{h(MO)}^{(1)}$	Data output hold time	Slave mode (after enable edge)	15	-	
		Master mode (after enable edge)	2	-	

1. Guaranteed by characterization results.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Table 54. I²S characteristics

Symbol	Parameter	Conditions		Min	Max	Unit
DuCy(SCK)	I2S slave input clock duty cycle	Slave mode		30	70	%
f_{CK} $1/t_{c(CK)}$	I ² S clock frequency	Master mode (data: 16 bits, Audio frequency = 48 kHz)		1.522	1.525	MHz
		Slave mode		0	6.5	
$t_{r(CK)}$ $t_{f(CK)}$	I ² S clock rise and fall time	Capacitive load C _L = 50 pF		-	8	ns
$t_{v(WS)}^{(1)}$	WS valid time	Master mode		3	-	
$t_{h(WS)}^{(1)}$	WS hold time	Master mode	I2S2	2	-	
			I2S3	0	-	
$t_{su(WS)}^{(1)}$	WS setup time	Slave mode		4	-	
$t_{h(WS)}^{(1)}$	WS hold time	Slave mode		0	-	
$t_{w(CKH)}^{(1)}$	CK high and low time	Master f _{PCLK} = 16 MHz, audio frequency = 48 kHz		312.5	-	
$t_{w(CKL)}^{(1)}$				345	-	
$t_{su(SD_MR)}^{(1)}$	Data input setup time	Master receiver	I2S2	2	-	
			I2S3	6.5	-	
$t_{su(SD_SR)}^{(1)}$	Data input setup time	Slave receiver		1.5	-	
$t_{h(SD_MR)}^{(1)(2)}$	Data input hold time	Master receiver		0	-	
$t_{h(SD_SR)}^{(1)(2)}$		Slave receiver		0.5	-	
$t_{v(SD_ST)}^{(1)(2)}$	Data output valid time	Slave transmitter (after enable edge)		-	18	
$t_{h(SD_ST)}^{(1)}$	Data output hold time	Slave transmitter (after enable edge)		11	-	
$t_{v(SD_MT)}^{(1)(2)}$	Data output valid time	Master transmitter (after enable edge)		-	3	
$t_{h(SD_MT)}^{(1)}$	Data output hold time	Master transmitter (after enable edge)		0	-	

1. Guaranteed by design and/or characterization results.

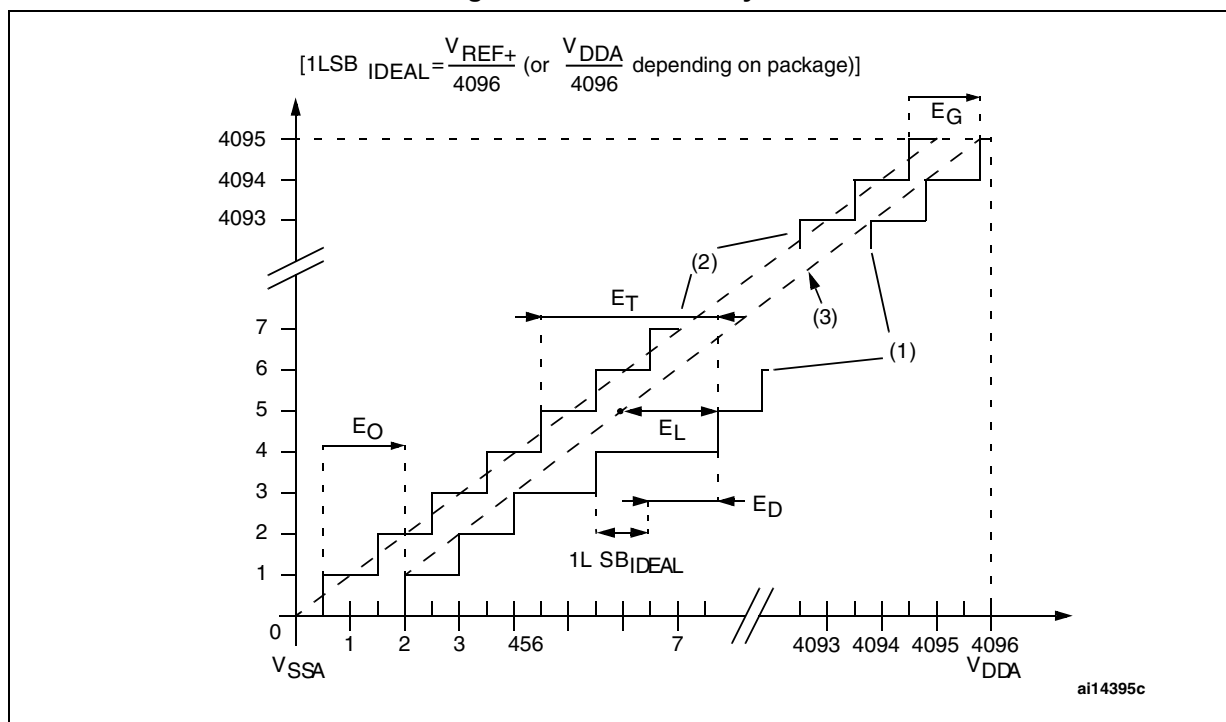
2. Depends on f_{PCLK} . For example, if $f_{PCLK} = 8$ MHz, then $T_{PCLK} = 1/f_{PCLK} = 125$ ns.

Table 62. ADC accuracy^{(1) (2)(3)}

Symbol	Parameter	Test conditions	Typ	Max ⁽⁴⁾	Unit
ET	Total unadjusted error	f _{PCLK2} = 56 MHz, f _{ADC} = 14 MHz, R _{AIN} < 10 kΩ, V _{DDA} = 2.4 V to 3.6 V Measurements made after ADC calibration	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±1.5	±3	

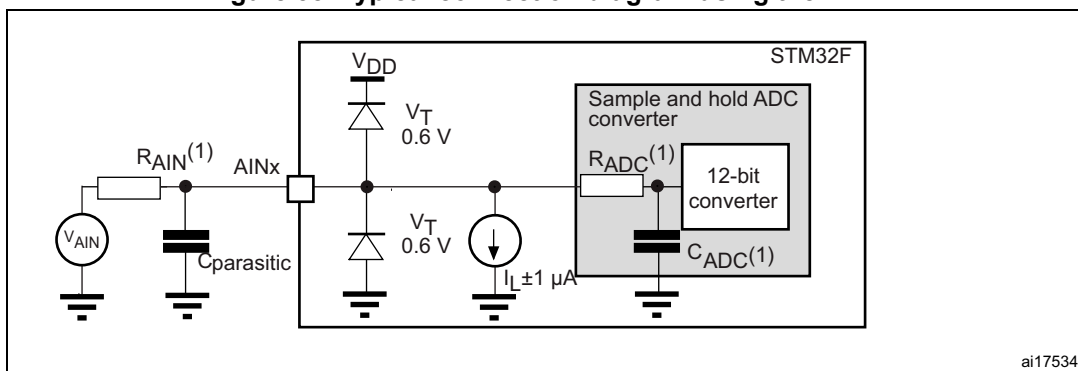
1. ADC DC accuracy values are measured after internal calibration.
2. Better performance could be achieved in restricted V_{DD}, frequency, V_{REF} and temperature ranges.
3. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in [Section 5.3.14](#) does not affect the ADC accuracy.
4. Guaranteed by characterization results.

Figure 57. ADC accuracy characteristics



1. Example of an actual transfer curve.
2. Ideal transfer curve.
3. End point correlation line.
4. ET = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
EO = Offset Error: deviation between the first actual transition and the first ideal one.
EG = Gain Error: deviation between the last ideal transition and the last actual one.
ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

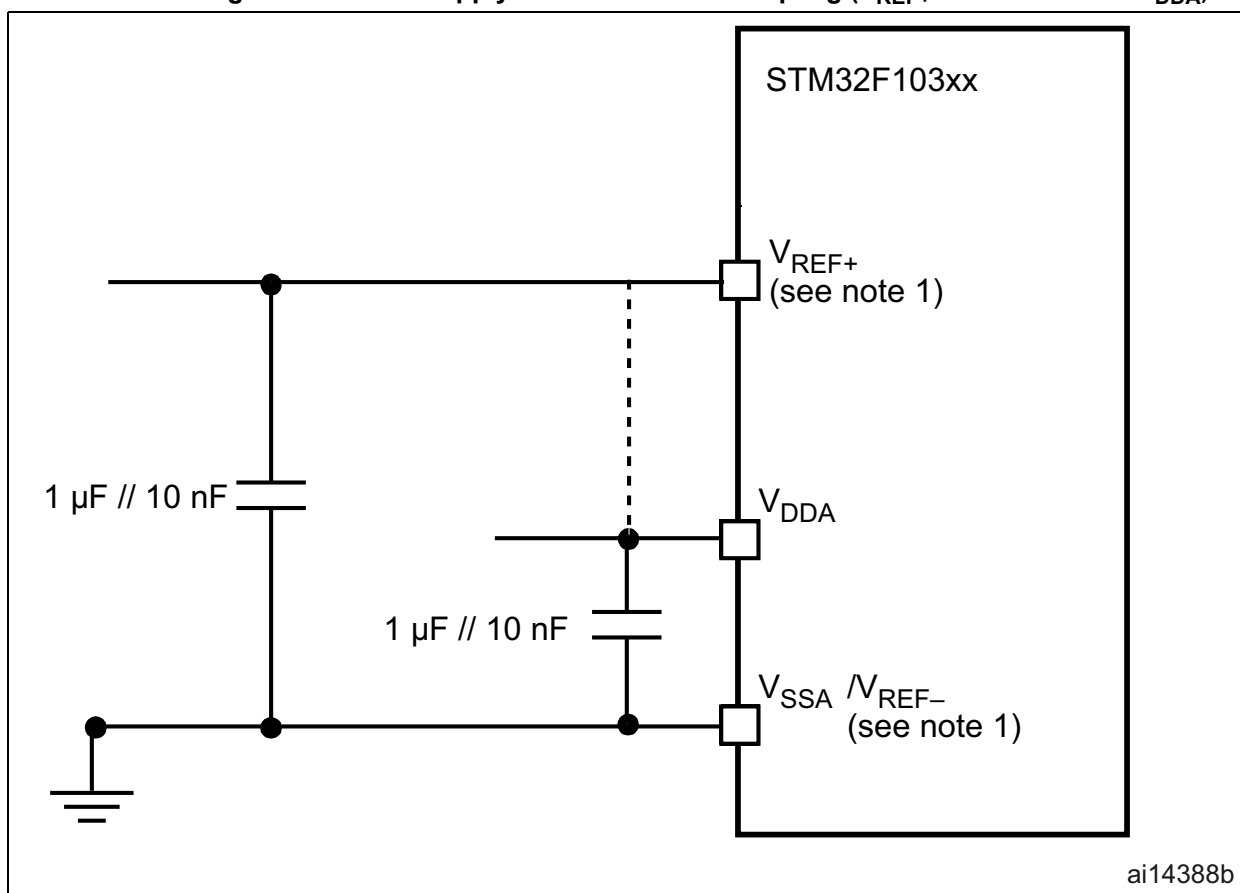
Figure 58. Typical connection diagram using the ADC



1. Refer to [Table 59](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

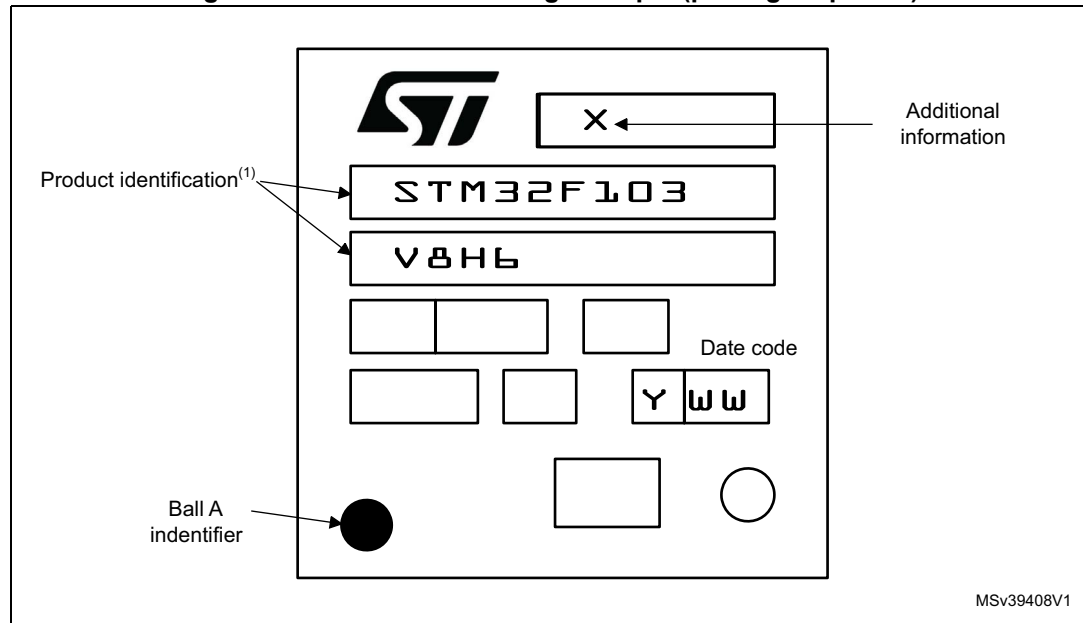
Power supply decoupling should be performed as shown in [Figure 59](#) or [Figure 60](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 59. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})

1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

Device marking for LFBGA100 package

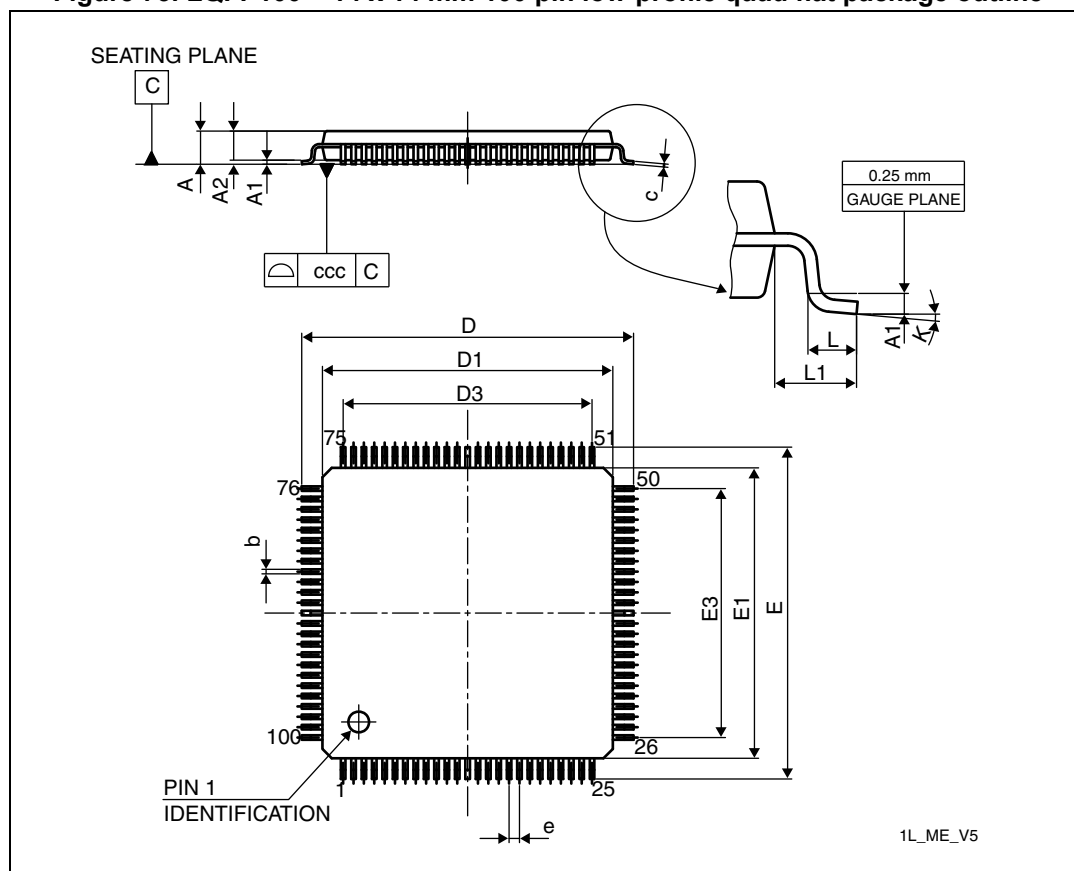
The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Figure 67. LFBGA100 marking example (package top view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.5 LQFP100 package information

Figure 73. LQFP100 – 14 x 14 mm 100 pin low-profile quad flat package outline



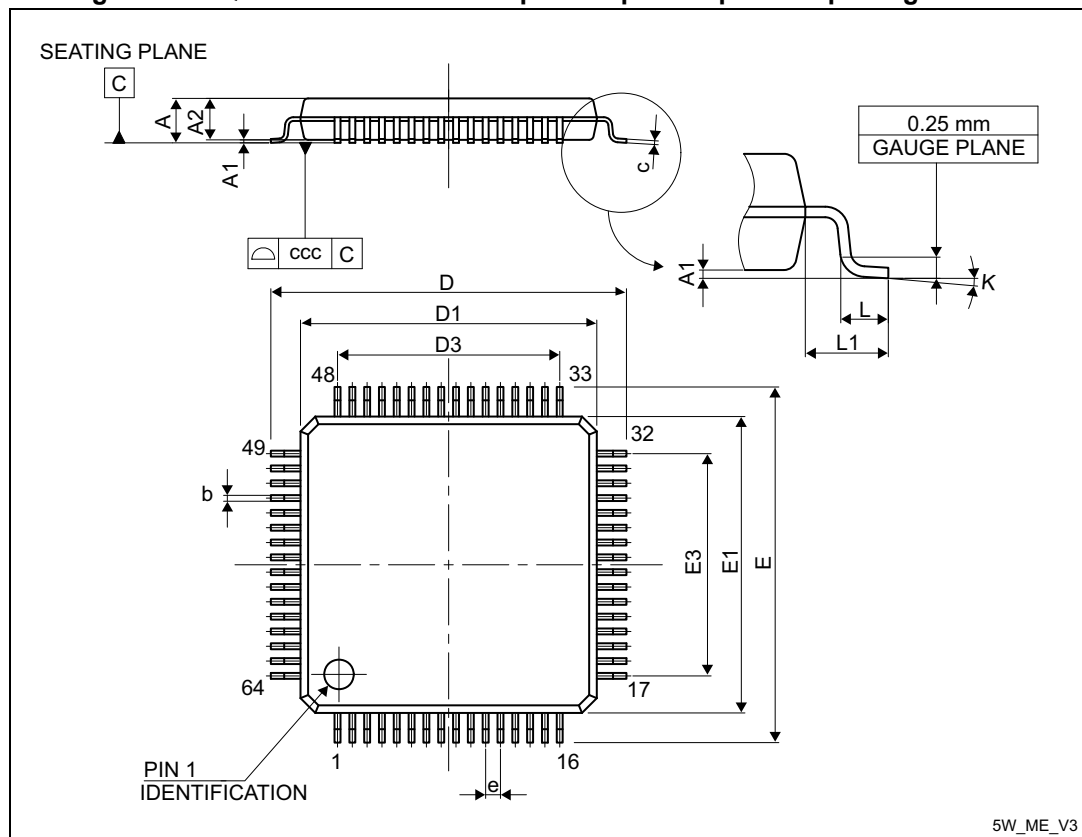
1. Drawing is not to scale.

Table 72. LQFP100 – 14 x 14 mm 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-

6.6 LQFP64 package information

Figure 76. LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package outline



1. Drawing is not in scale.

Table 73. LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

Table 76. Document revision history

Date	Revision	Changes
19-Apr-2011	8	Updated package choice for 103Rx in Table 2 Updated footnotes below Table 7: Voltage characteristics on page 43 and Table 8: Current characteristics on page 43 Updated $t_{w\ min}$ in Table 21: High-speed external user clock characteristics on page 58 Updated startup time in Table 24: LSE oscillator characteristics (fLSE = 32.768 kHz) on page 61 Updated note 2 in Table 51: I2C characteristics on page 97 Updated Figure 48: I2C bus AC waveforms and measurement circuit Updated Figure 47: Recommended NRST pin protection Updated Section 5.3.14: I/O port characteristics Updated Table 35: Synchronous multiplexed NOR/PSRAM read timings on page 73 Updated FSMC Figure 26 thru Figure 31 Updated Figure 41.: NAND controller waveforms for common memory write access and Figure 48.: I2C bus AC waveforms and measurement circuit Added Section 5.3.13: I/O current injection characteristics Updated Figure 67 and added Table 69: WLCSP, 64-ball 4.466 × 4.395 mm, 0.500 mm pitch, wafer-level chip-scale package mechanical data on page 121 LQFP64 package mechanical data updated: see Figure 73.: LQFP64 – 10 × 10 mm 64 pin low-profile quad flat package outline and Table 73: LQFP64 – 10 × 10 mm 64 pin low-profile quad flat package mechanical data on page 130.
30-Sept-2014	9	Added Note 7 in Table 5: High-density STM32F103xC/D/E pin definitions on page 31. Updated Note 10 in Table 5: High-density STM32F103xC/D/E pin definitions on page 31. Modified Note 2 in Table 62: ADC accuracy on page 109 Modified Note 3 in Table 62: ADC accuracy on page 109 Modified notes in Table 51: I2C characteristics on page 97 Updated Figure 51: SPI timing diagram - master mode(1) on page 101
23-Feb-2015	10	Updated Figure 66.: BGA pad footprint, Figure 70: LQFP144 - 144-pin, 20 × 20 mm low-profile quad flat package outline, Figure 73.: LQFP100 – 14 × 14 mm 100 pin low-profile quad flat package outline, Figure 74.: LQFP100 recommended footprint, Figure 76.: LQFP64 – 10 × 10 mm 64 pin low-profile quad flat package outline, Figure 77.: LQFP64 - 64-pin, 10 × 10 mm low-profile quad flat recommended footprint Added Figure 72.: LQFP144 marking example (package top view), Figure 75.: LQFP100 marking example (package top view), Figure 78.: LQFP64 marking example (package top view) Updated Table 72: LQFP100 – 14 × 14 mm 100-pin low-profile quad flat package mechanical data, Table 73: LQFP64 – 10 × 10 mm 64 pin low-profile quad flat package mechanical data